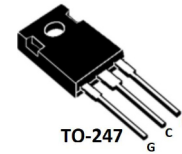


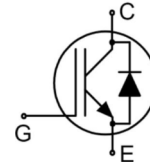
Features

- Low gate charge
- Trench-Stop Technology
- High speed switching
- Saturation voltage: $V_{CE(sat)}$, typ= 1.5V @ $I_C=50A$ and $T_C=25^{\circ}C$



Applications

- General purpose inverters
- Induction heating(IH)
- Welding Converters
- UPS



Absolute Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	MSG60T65HHC0	Unit
Collector-Emmitter Voltage	V_{ces}	650	V
Collector Current-continuous	I_C $T=25^{\circ}C$ $T=100^{\circ}C$	120	A
		60	A
Diode Forward current, limited by T_{jmax}	I_F $T=25^{\circ}C$ $T=100^{\circ}C$	120	A
		60	A
Collector Current-pulse(note 1)	I_{CM}	240	A
Continuous Gate-Emmitter Voltage	V_{GE}	± 20	V
Transient Gate-emitter voltage	V_{GE}	± 30	V
Turn-off safe area	-	200	A
Power Dissipation	P_D $T_C=25^{\circ}C$	260	W
Operating Temperature Range	T_J	$-55 \sim 175$	$^{\circ}C$
Storage Temperature Range	T_{STG}	$-55 \sim 175$	$^{\circ}C$
Maximum Lead Temperature for Soldering Purposes	T_L	300	$^{\circ}C$

Thermal Characteristic

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Off-Characteristics						
Collector-Emmitter Voltage	BV_{CES}	$I_C=250\mu A, V_{GE}=0V$	650	-	-	V
		$I_C=1mA, V_{GE}=0V$	650			V

MSG60T65HHC0

Zero Gate Voltage Collector Current	I _{CES}	V _{CE} =650V,V _{GE} =0V, T _C =25°C	-	0.1	40	μA
		TC=150°C	-	2.25	-	μA
Gate-body leakage current	I _{GESF}	V _{CE} =0V,V _{GE} =± 20V	-	-	200	nA
On-Characteristics						
Gate-Emmitter Threshold Voltage	V _{GE(th)}	VCE=VGE, Ic=250uA	3.0	5.0	6.0	V
Collector-Emmitter saturation Voltage	V _{CESAT}	V _{GE} =15V,I _C =50A	-	1.5	-	V
Dynamic Characteristics						
Input capacitance	Cies	VCE=25V, VGE=0V, f=1.0MHZ	-	3510	-	pF
Output capacitance	Coes		-	244	-	pF
Reverse transfer capacitance	Cres		-	81	-	pF
Switching Characteristics						
Turn-On delay time	t _{d(on)}	V _{CC} =400V,Ic=60A, R _G =10Ω, V _{GE} =0.0/15.0V Tc=25°C Inductive Load	-	36	-	ns
Turn-On rise time	t _r		-	96	-	ns
Turn-off delay time	t _{d(off)}		-	101	-	ns
Turn-off Fall time	t _f		-	55	-	ns
Turn-on energy	E _{on}		-	1.65	-	mJ
Turn-off energy	E _{off}		-	1.1	-	mJ
Total switching Energy	E _{total}		-	2.75	-	mJ
Turn-On delay time	t _{d(on)}	V _{CC} =400V,Ic=60A, R _G =10Ω, V _{GE} =0.0/15.0V Tc=75°C Inductive Load	-	33	-	ns
Turn-On rise time	t _r		-	108	-	ns
Turn-off delay time	t _{d(off)}		-	130	-	ns
Turn-off Fall time	t _f		-	105	-	ns
Turn-on energy	E _{on}		-	1.9	-	mJ
Turn-off energy	E _{off}		-	1.5	-	mJ
Total switching Energy	E _{total}		-	3.4	-	mJ
Total Gate Charge	Qg	VCE=480V,Ic=60A ,VGE=15V	-	132	-	nC
Gate to emitter Charge	Qge			33		nC
Gate to Collector charge	Qgc			55		nC

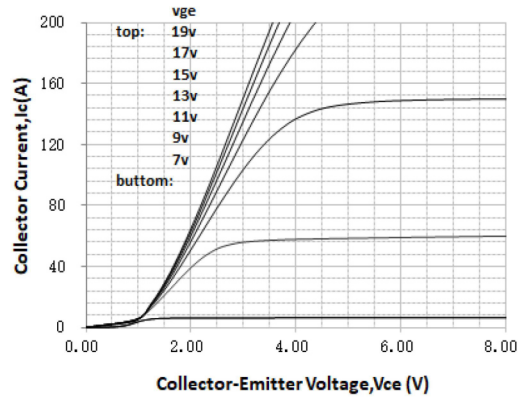
Anti-Paraller Diode Characteristics and Maximum Ratings						
Diode Forward Voltage	V _F	V _{GE} =0V, I _F =30A	-	-	1.4	V
Diode Forward Current	I _F	T _C =100°C	-	-	60	A
Diode Reverse recovery time	t _{rr}	V _{GE} =0V, V _R =300V I _F =40A di=dt=600/us (note 4)	-	90	-	ns
Reverse recovery charge	Q _{rr}		-	900	-	nC
Reverse Recovery Current	I _{rr}		-	17	-	A

Thermal Characteristic

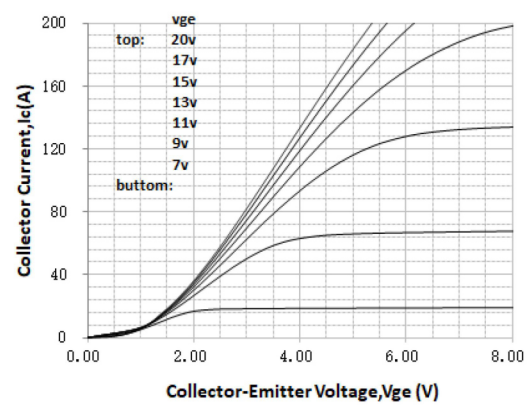
Parameter	Symbol	Max	Unit
IGBT Thermal Resistance, Junction to Case	R _{th(j-c)}	0.48	°C/W
Diode Thermal Resistance, Junction to Case	R _{th(j-c)}	1.1	°C/W
Thermal Resistance, Junction to Ambient	R _{th(j-A)}	40	°C/W

Electrical Characteristics (curves)

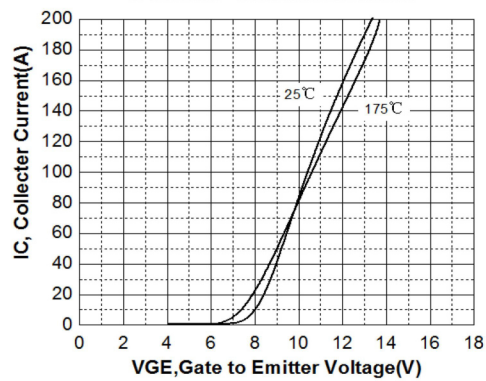
Output Characteristics (25°C)



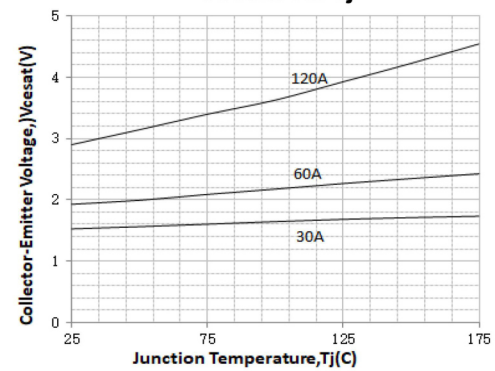
Output Characteristics (175°C)



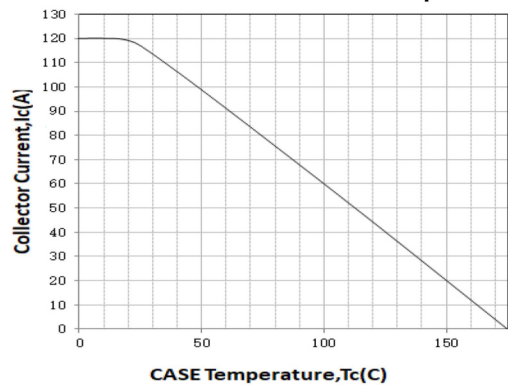
Transfer Characteristics



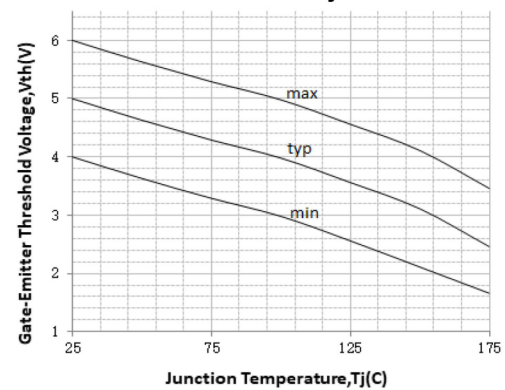
Vcesat vs. Tj



Collector current vs. case temperature

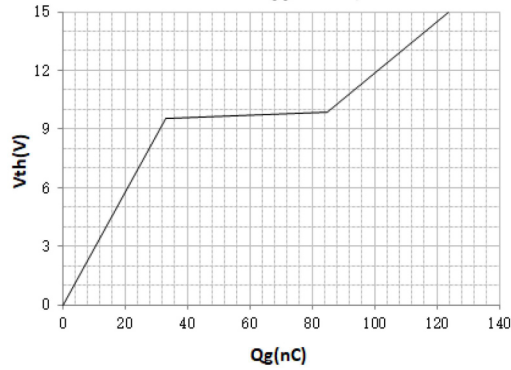


VTH vs. Tj



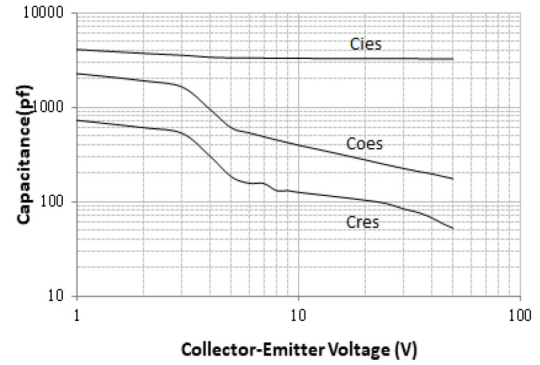
Gate Charge Characteristics

VGE=15V, VCC=480V, IC=60A



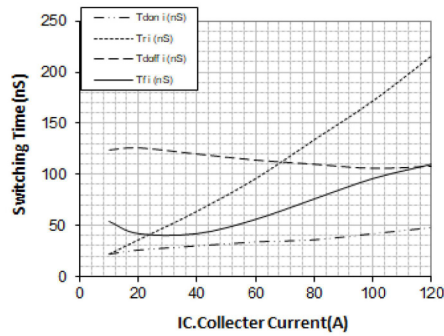
Capacitance Characteristic

VGE =0V, f=1.0MHZ



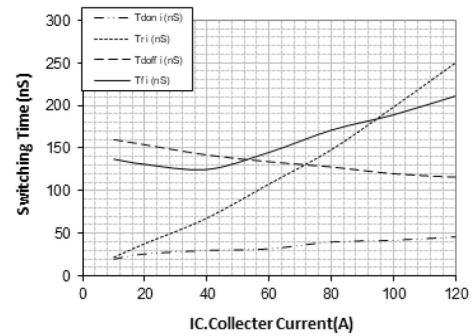
Switching Time vs. IC(25°C)

VCE=400V, VGE=15V, RG=10Ω



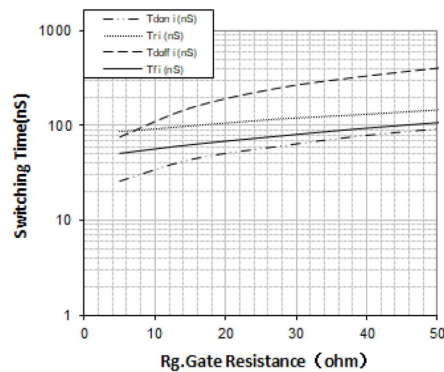
Switching Time vs. IC(175°C)

VCE=400V, VGE=15V, RG=10Ω



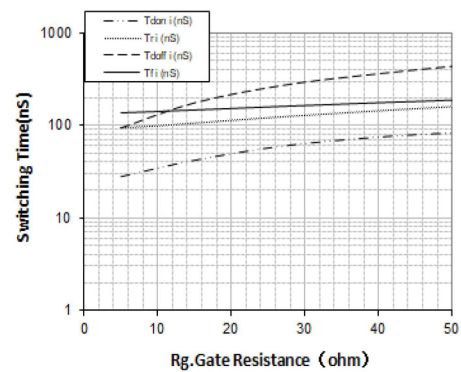
Switching Time vs. Rg(25°C)

VGE=15V, VCE=400V, IC=60A



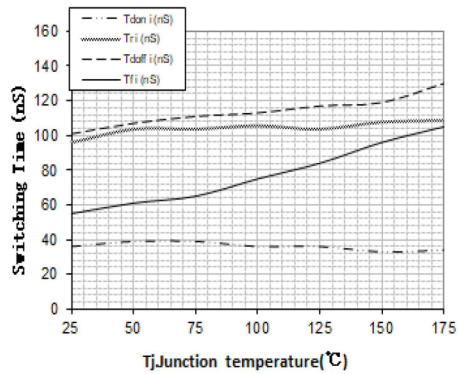
Switching Time vs. Rg(175°C)

VGE=15V, VCE=400V, IC=60A

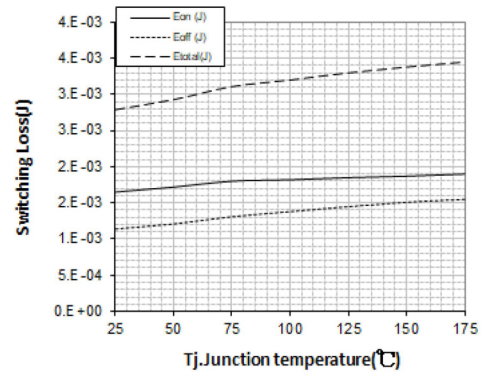


Switching Time vs. Tj

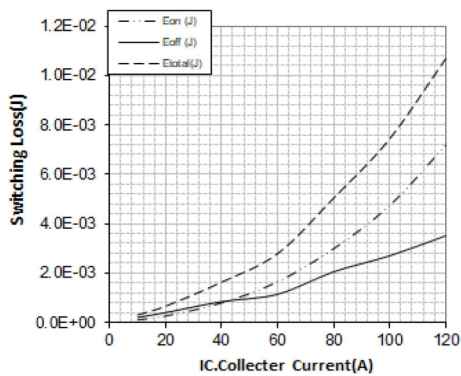
VGE=15V, VCE=400V, IC=60A, Rg=10Ω

**Switching Loss vs. Tj**

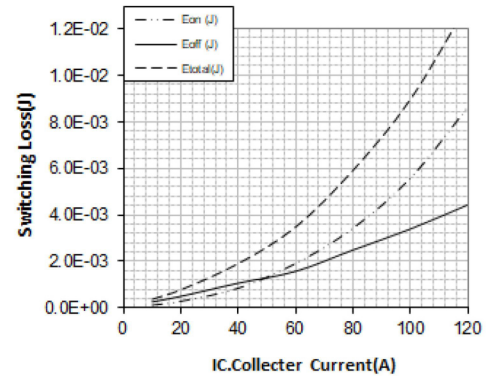
VGE=15V, VCE=400V, IC=60A, Rg=10Ω

**Switching Loss vs. IC(25°C)**

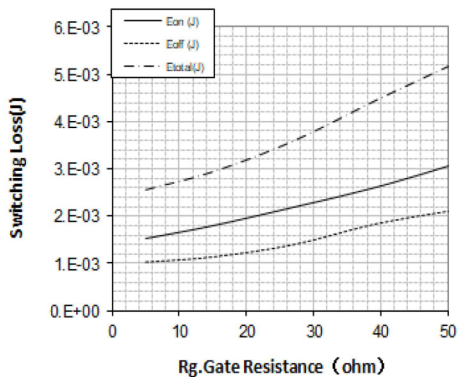
VGE=15V, VCE=400V, Rg=10Ω

**Switching Loss vs. IC(175°C)**

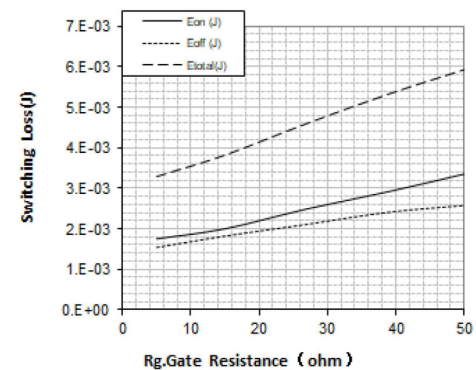
VGE=15V, VCE=400V, Rg=10Ω

**Switching Loss vs. Rg(25°C)**

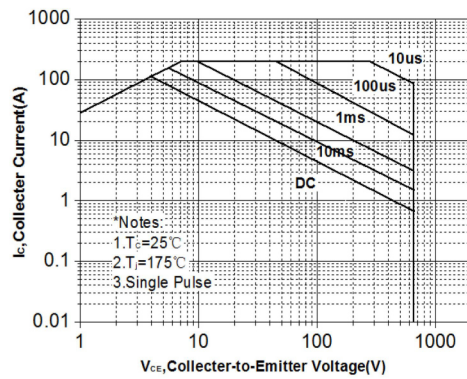
VGE=15V, VCE=400V, IC=60A

**Switching Loss vs. Rg(175°C)**

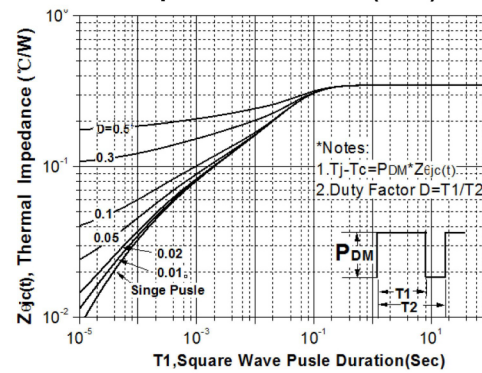
VGE=15V, VCE=400V, IC=60A



Forward Bias SOA



Normalized Maximum Transient Thermal Impedance for IGBT(RJC)



Package Mechanical DATA

